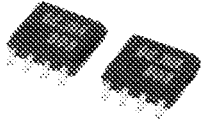


MITSUBISHI Nch POWER MOSFET

FY6ACJ-03A

HIGH-SPEED SWITCHING USE

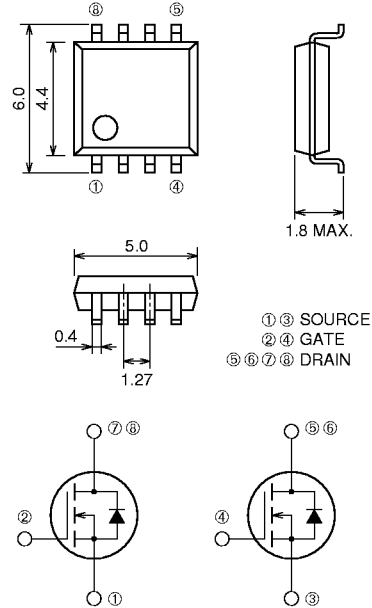
FY6ACJ-03A



- 4V DRIVE
- V_{DS} 30V
- $r_{DS(ON)}$ (MAX) 23m Ω
- I_D 6A

OUTLINE DRAWING

Dimensions in mm



SOP-8

APPLICATION

Motor control, Lamp control, Solenoid control
DC-DC converter, etc.

MAXIMUM RATINGS (T_c = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V_{DS}	Drain-source voltage	$V_{GS} = 0V$	30	V
V_{GSS}	Gate-source voltage	$V_{DS} = 0V$	± 20	V
I_D	Drain current		6	A
I_{DM}	Drain current (Pulsed)		42	A
I_{DA}	Avalanche drain current (Pulsed)	$L = 10\mu H$	6	A
I_S	Source current		1.7	A
I_{SM}	Source current (Pulsed)		6.8	A
P_D	Maximum power dissipation		1.8	W
T_{ch}	Channel temperature		-55 ~ +150	°C
T_{stg}	Storage temperature		-55 ~ +150	°C
—	Weight	Typical value	0.07	g

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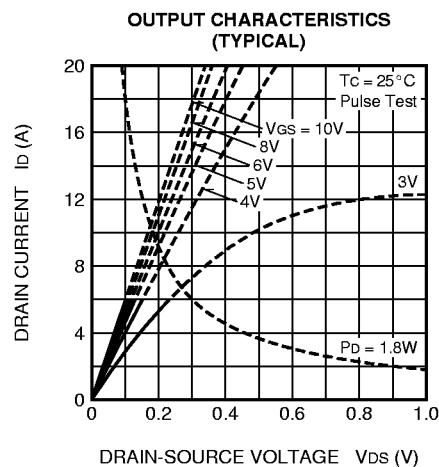
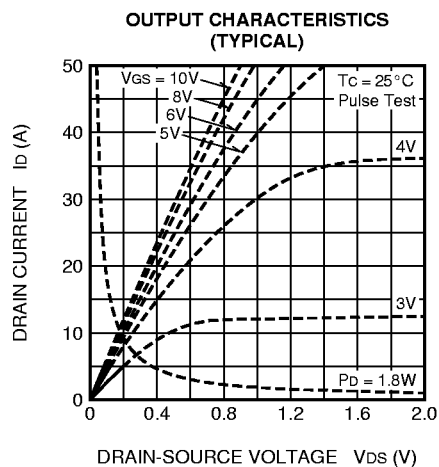
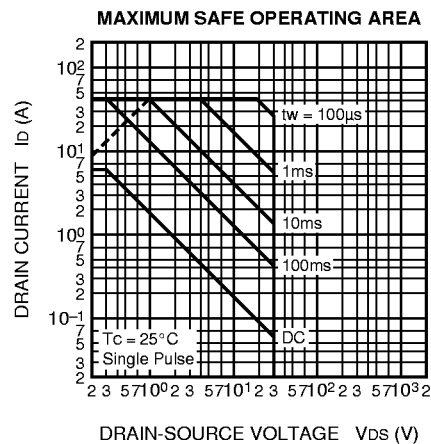
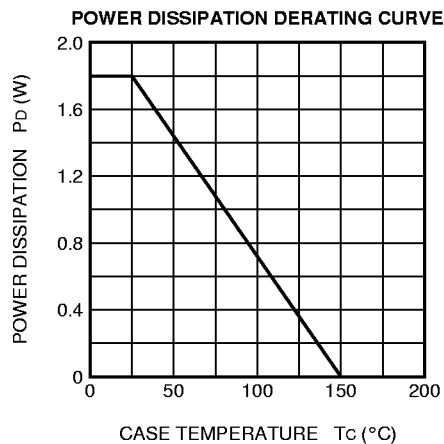
FY6ACJ-03A

HIGH-SPEED SWITCHING USE

ELECTRICAL CHARACTERISTICS (T_{ch} = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V _{(BR)DSS}	Drain-source breakdown voltage	I _D = 1mA, V _{GS} = 0V	30	—	—	V
I _{GSS}	Gate-source leakage current	V _{GS} = ±20V, V _{DS} = 0V	—	—	±0.1	μA
I _{DSS}	Drain-source leakage current	V _{DS} = 30V, V _{GS} = 0V	—	—	0.1	mA
V _{GS(th)}	Gate-source threshold voltage	I _D = 1mA, V _{DS} = 10V	1.0	1.5	2.0	V
r _{DS(ON)}	Drain-source on-state resistance	I _D = 6A, V _{GS} = 10V	—	17	23	mΩ
r _{DS(ON)}	Drain-source on-state resistance	I _D = 3A, V _{GS} = 4V	—	26	40	mΩ
V _{DS(ON)}	Drain-source on-state voltage	I _D = 6A, V _{GS} = 10V	—	102	138	mV
y _{fs}	Forward transfer admittance	I _D = 6A, V _{DS} = 10V	—	12	—	S
C _{iss}	Input capacitance	V _{DS} = 10V, V _{GS} = 0V, f = 1MHz	—	1000	—	pF
C _{oss}	Output capacitance		—	350	—	pF
C _{rss}	Reverse transfer capacitance		—	160	—	pF
t _{d(on)}	Turn-on delay time	V _{DD} = 15V, I _D = 3A, V _{GS} = 10V, R _{GEN} = R _{GS} = 50Ω	—	15	—	ns
t _r	Rise time		—	25	—	ns
t _{d(off)}	Turn-off delay time		—	75	—	ns
t _f	Fall time		—	55	—	ns
V _{SD}	Source-drain voltage	I _S = 1.7A, V _{GS} = 0V	—	0.75	1.10	V
R _{th(ch-a)}	Thermal resistance	Channel to ambient	—	—	69.4	°C/W
t _{rr}	Reverse recovery time	I _S = 1.7A, di _s /dt = -50A/μs	—	35	—	ns

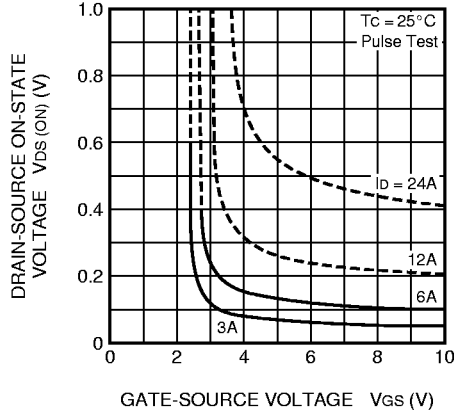
PERFORMANCE CURVES



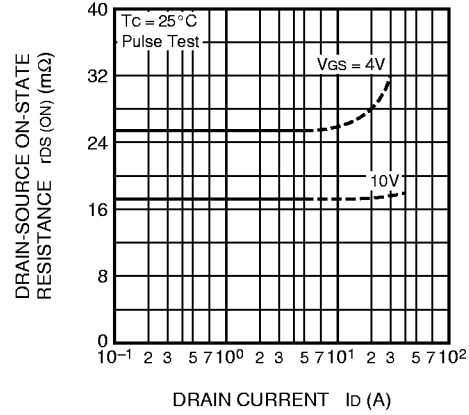
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HIGH-SPEED SWITCHING USE

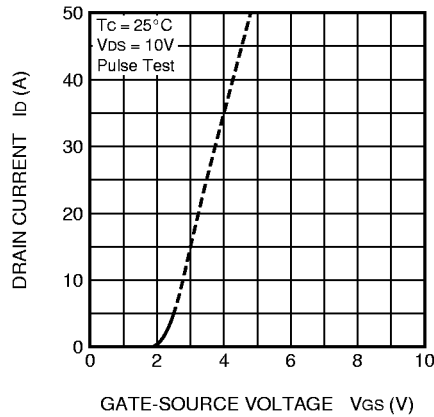
ON-STATE VOLTAGE VS.
GATE-SOURCE VOLTAGE
(TYPICAL)



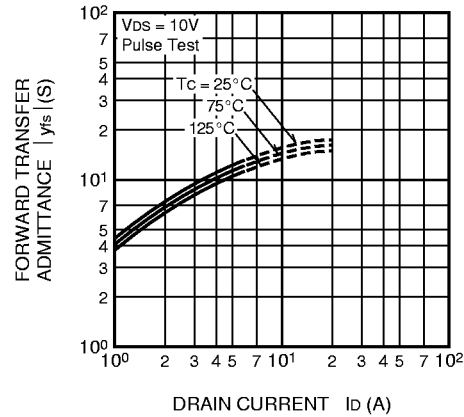
ON-STATE RESISTANCE VS.
DRAIN CURRENT
(TYPICAL)



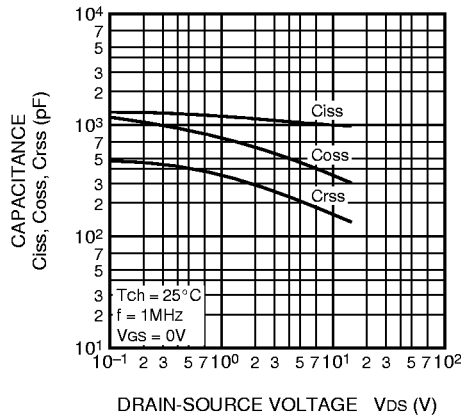
TRANSFER CHARACTERISTICS
(TYPICAL)



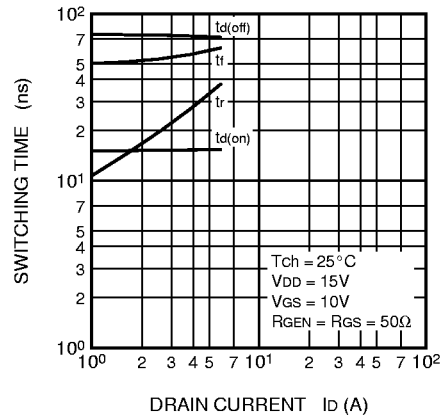
FORWARD TRANSFER ADMITTANCE
VS. DRAIN CURRENT
(TYPICAL)



CAPACITANCE VS.
DRAIN-SOURCE VOLTAGE
(TYPICAL)



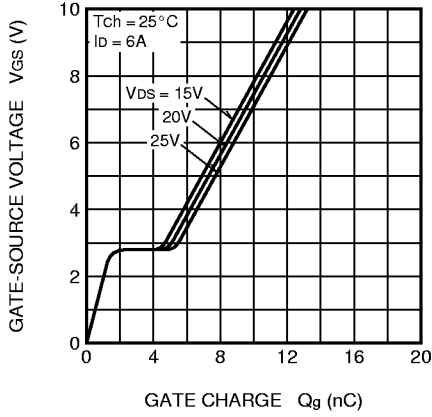
SWITCHING CHARACTERISTICS
(TYPICAL)



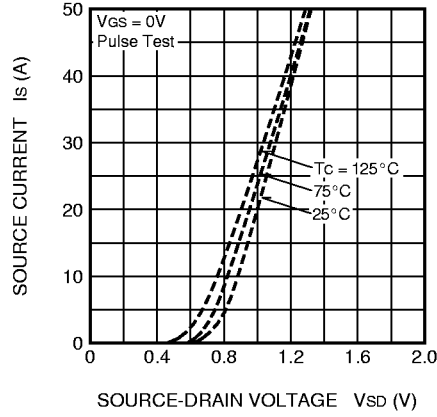
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HIGH-SPEED SWITCHING USE

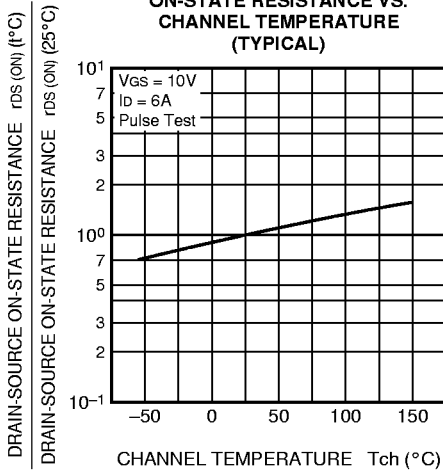
**GATE-SOURCE VOLTAGE
VS. GATE CHARGE
(TYPICAL)**



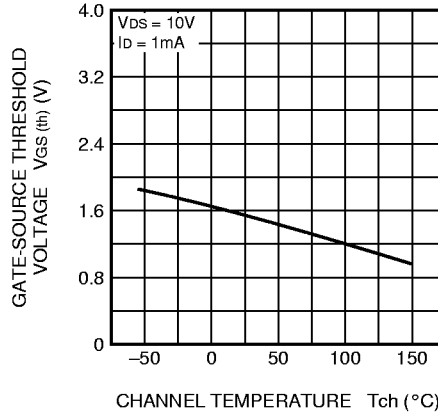
**SOURCE-DRAIN DIODE
FORWARD CHARACTERISTICS
(TYPICAL)**



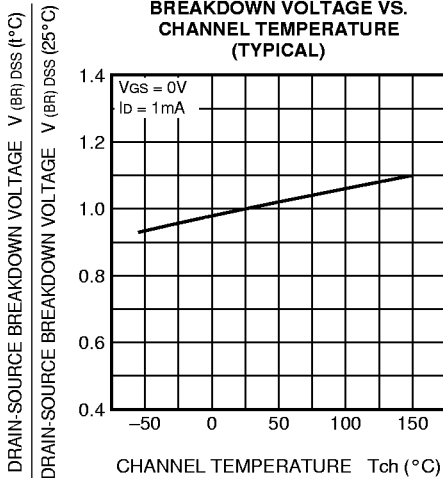
**ON-STATE RESISTANCE VS.
CHANNEL TEMPERATURE
(TYPICAL)**



**THRESHOLD VOLTAGE VS.
CHANNEL TEMPERATURE
(TYPICAL)**



**BREAKDOWN VOLTAGE VS.
CHANNEL TEMPERATURE
(TYPICAL)**



**TRANSIENT THERMAL IMPEDANCE
CHARACTERISTICS**

